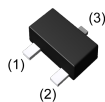
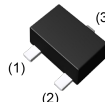


Parameter	Value
V_{CEO}	30V
I_C	0.5A

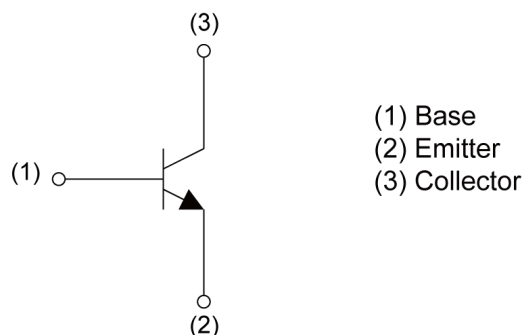
●Outline

EMT3F  2SCR502EB SOT-416FL	UMT3F  2SCR502UB SOT-323FL
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●Features

- 1)General purpose.
- 2)Complementary PNP types :
2SAR502EB(EMT3F)/2SAR502UB(UMT3F)
- 3)Collector current is large.
- 4)Low $V_{CE(sat)}$.

●Inner circuit



●Application

LOW FREQUENCY AMPLIFIER

●Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
2SCR502EB	EMT3F	1616	TL	180	8	3000	LW
2SCR502UB	UMT3F	2021	TL	180	8	3000	LW

● **Absolute maximum ratings** ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Values	Unit
Collector-base voltage		V_{CBO}	30	V
Collector-emitter voltage		V_{CEO}	30	V
Emitter-base voltage		V_{EBO}	6	V
Collector current		I_C^{*1}	0.5	A
		I_{CP}^{*2}	1	A
Base current		I_B	0.15	A
Power dissipation	2SCR502EB	P_D^{*3}	150	mW
	2SCR502UB		200	
Junction temperature		T_j	150	°C
Range of storage temperature		T_{stg}	-55 to +150	°C

● **Electrical characteristics** ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector-base breakdown voltage	BV_{CBO}	$I_C = 100\mu\text{A}$	30	-	-	V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = 1\text{mA}$	30	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = 100\mu\text{A}$	6	-	-	V
Collector cut-off current	I_{CBO}	$V_{CB} = 25\text{V}$	-	-	200	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4\text{V}$	-	-	200	nA
Collector-emitter saturation voltage	$V_{CE(sat)}^{*4}$	$I_C = 200\text{mA}, I_B = 10\text{mA}$	-	100	300	mV
DC current gain	h_{FE}	$V_{CE} = 2\text{V}, I_C = 100\text{mA}$	200	-	500	-
Transition frequency	f_T^{*4}	$V_{CE} = 10\text{V}, I_E = -100\text{mA}, f = 100\text{MHz}$	-	360	-	MHz
Output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$	-	3	-	pF

*1 Limited by power dissipation.

*2 $P_w=10\text{ms}$, Single pulse.

*3 Each terminal mounted on a reference land.

*4 Pulsed

●Electrical characteristic curves($T_a = 25^\circ\text{C}$)

Fig.1 Grounded Emitter Propagation Characteristics

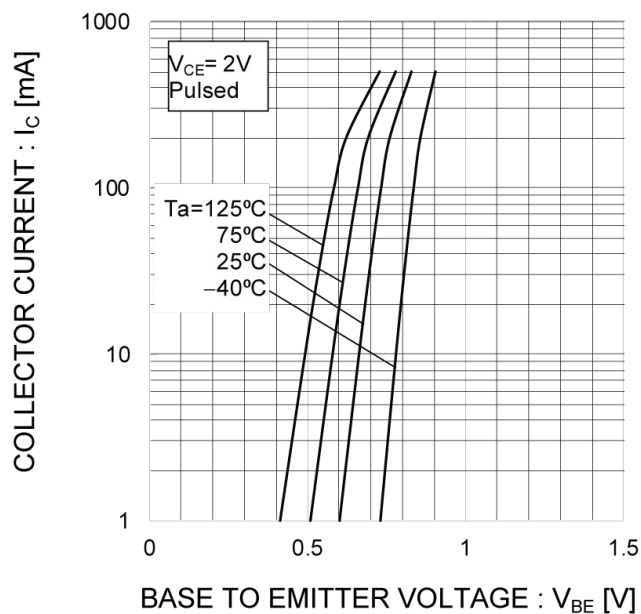


Fig.2 Typical Output Characteristics

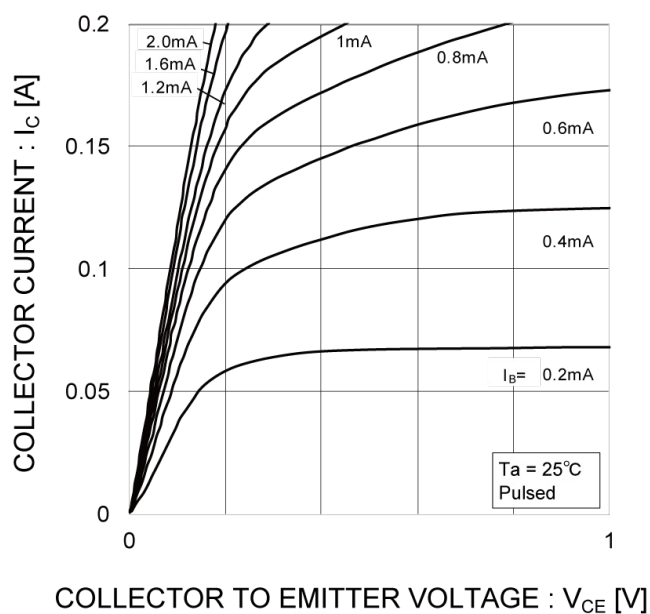


Fig.3 DC Current Gain vs. Collector Current(I)

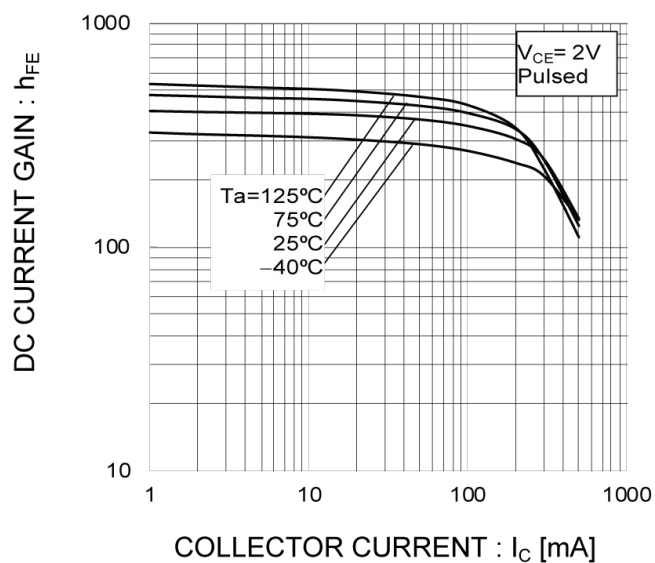
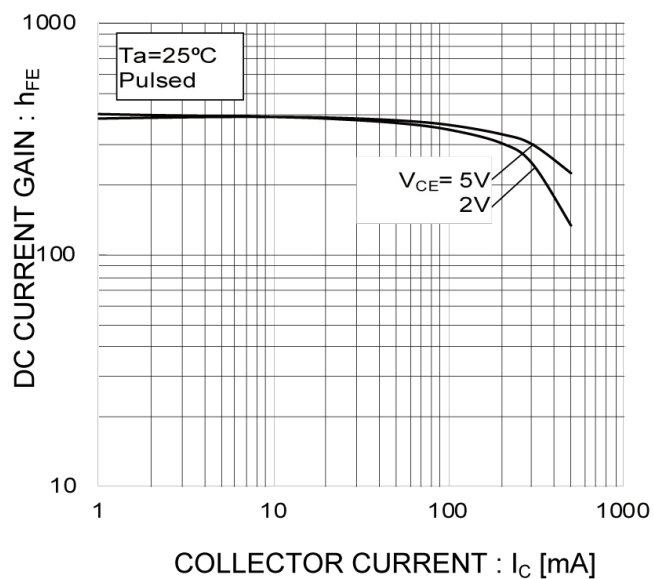


Fig.4 DC Current Gain vs. Collector Current(II)



●Electrical characteristic curves($T_a = 25^\circ\text{C}$)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current(I)

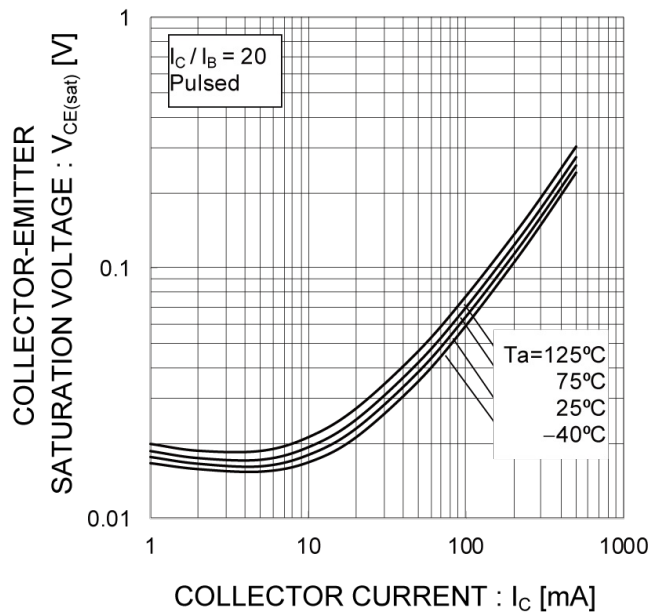


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current(II)

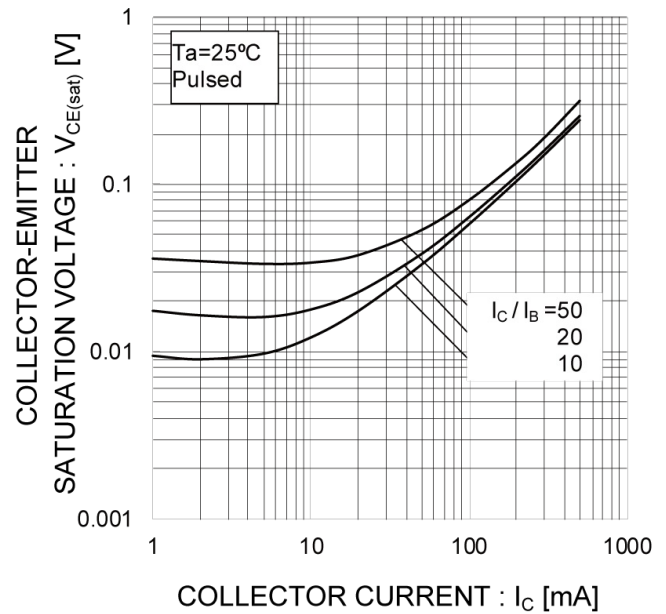


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

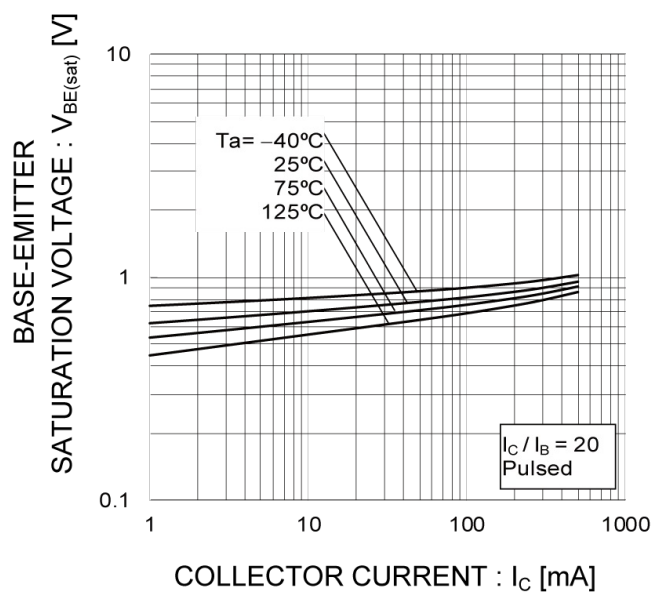
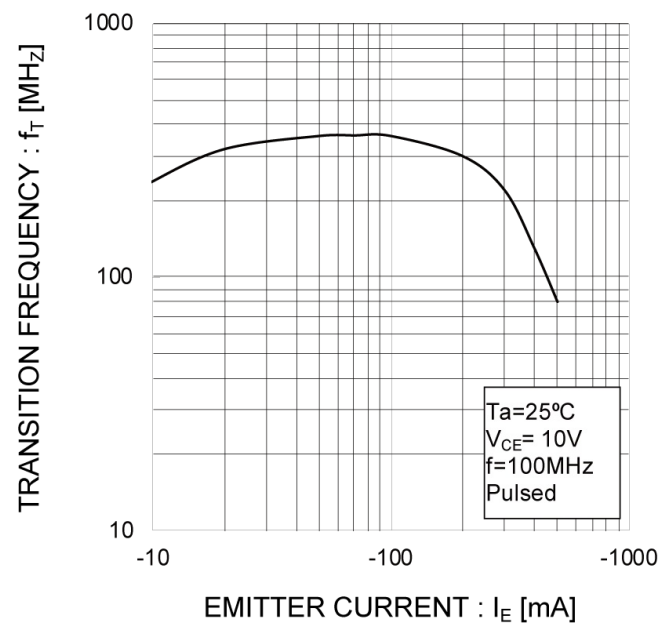


Fig.8 Gain Bandwidth Product vs. Emitter Current



●Electrical characteristic curves($T_a = 25^\circ\text{C}$)

Fig.9 Emitter input capacitance vs.
Emitter-Base Voltage Collector output
capacitance vs. Collector-Base Voltage

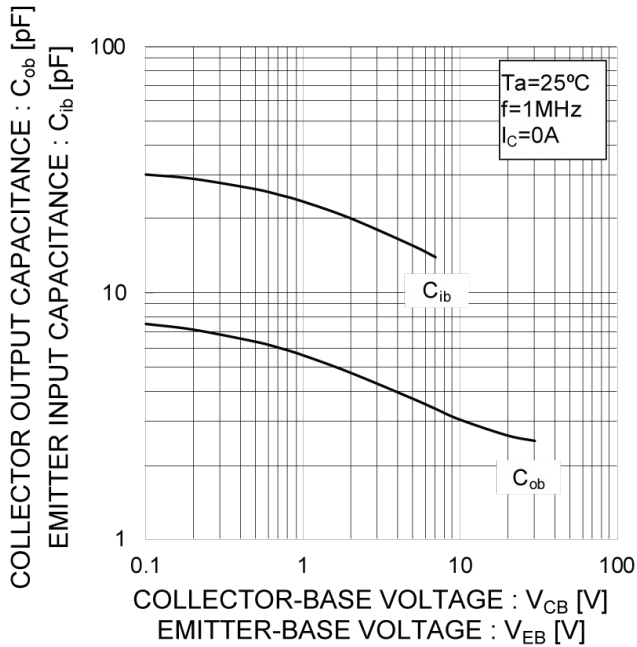


Fig.10 Safe Operating Area

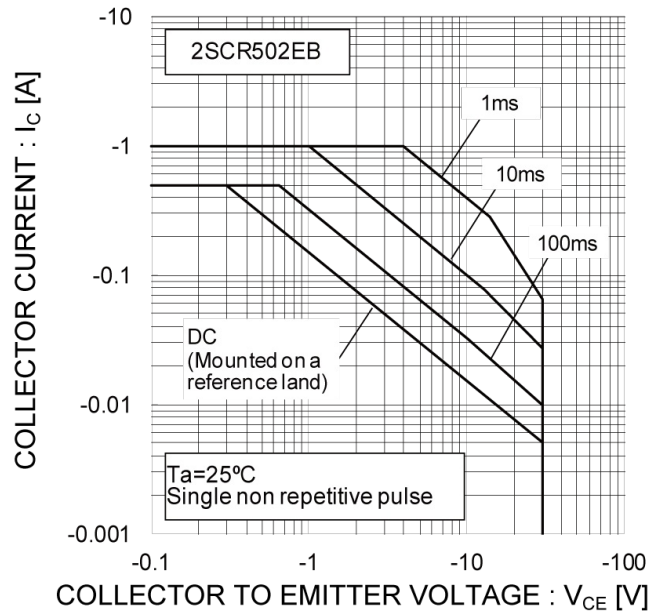
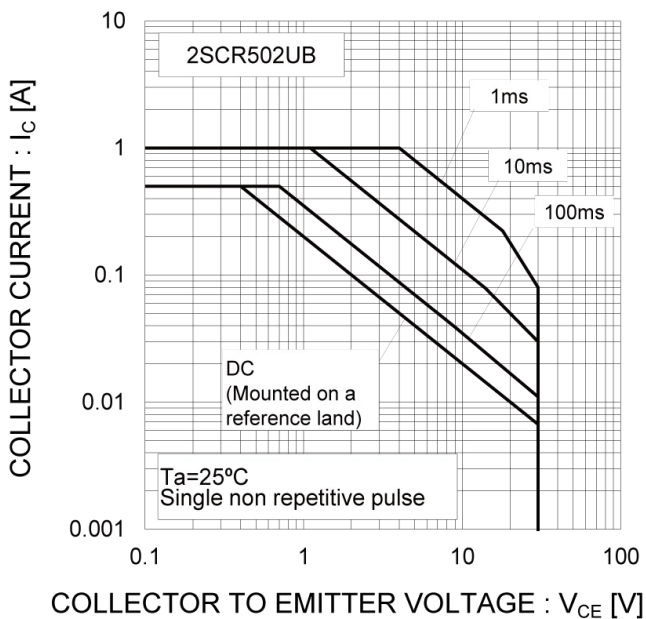
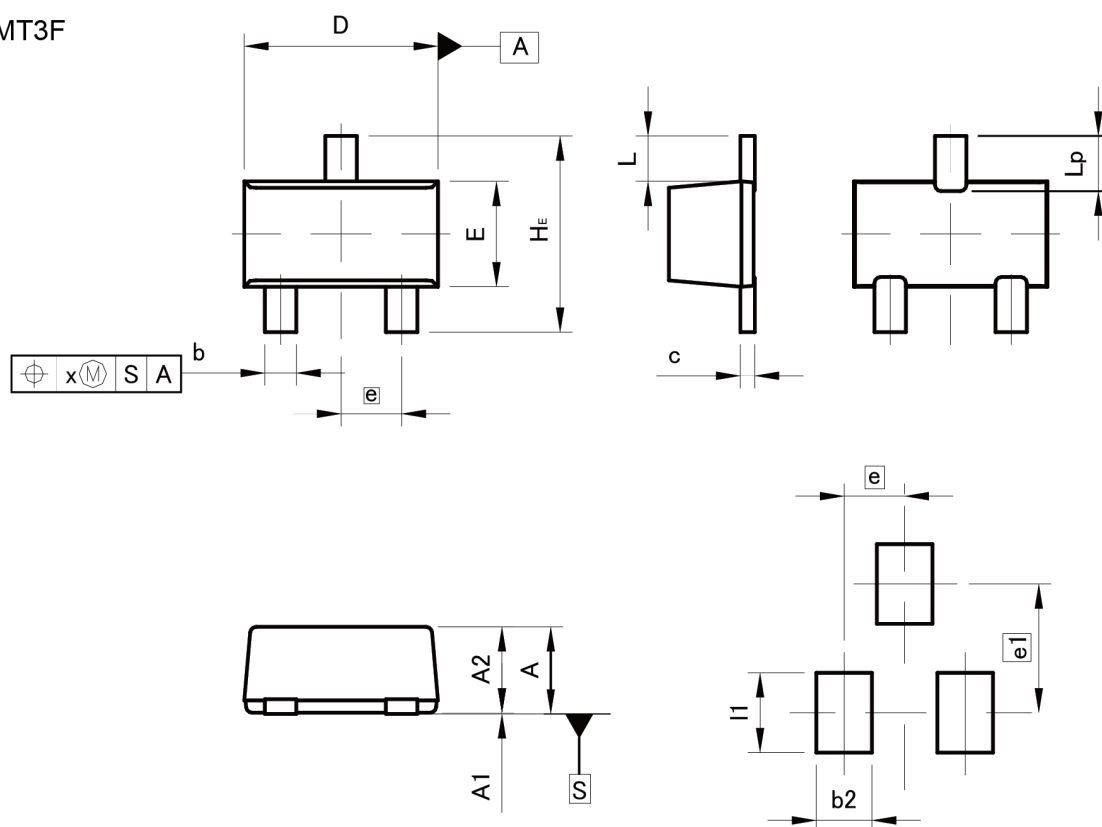


Fig.11 Safe Operating Area



●Dimensions

EMT3F



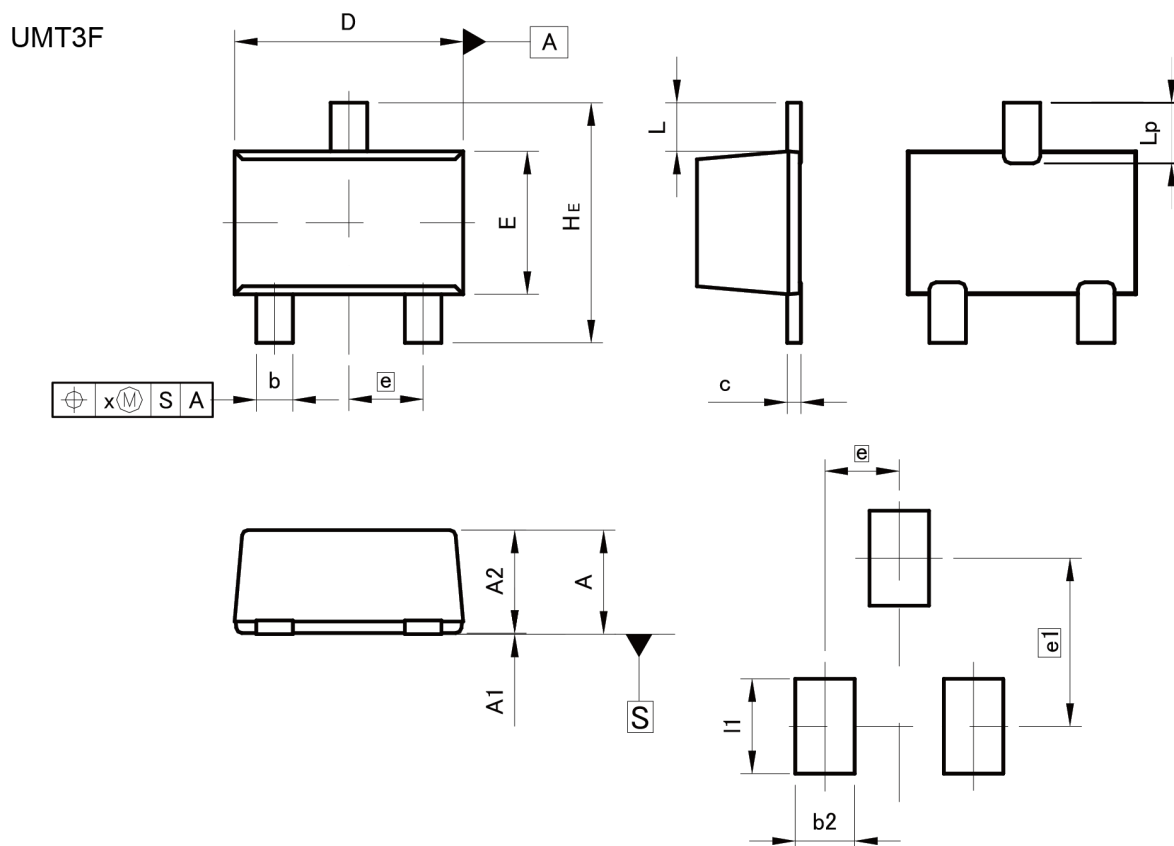
Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.65	0.85	0.026	0.033
A1	0.00	0.10	0.000	0.004
A2	0.60	0.80	0.024	0.031
b	0.21	0.36	0.008	0.014
c	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	0.76	0.96	0.030	0.038
e	0.50		0.020	
HE	1.50	1.70	0.059	0.067
L	0.37		0.015	
Lp	0.35	0.55	0.014	0.022
x	—	0.10	—	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	—	0.46	—	0.018
e1	—	1.05	—	0.041
l1	—	0.65	—	0.026

Dimension in mm/inches

●Dimensions



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.85	1.05	0.033	0.041
A1	0.00	0.10	0.000	0.004
A2	0.80	1.00	0.031	0.039
b	0.27	0.42	0.011	0.017
c	0.08	0.18	0.003	0.007
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
e	0.65		0.026	
HE	2.00	2.20	0.079	0.087
L	0.43		0.017	
Lp	0.43	0.63	0.017	0.025
x	—	0.10	—	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	—	0.52	—	0.020
e1	1.47		0.058	
l1	—	0.83	—	0.033

Dimension in mm/inches

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